

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3770	((257/E21.193) or (257/E21.165) or (257/E21.635)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 16:15
L2	2473	1 not (@ad>"20020418" or @rlad>"20020418")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 16:15
L3	389	2 and (gate near dielectric) same ("high-k" or (high))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 16:15
S1	4	((("5596214") or ("6278164")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 08:51
S2	85479	(high near voltage) and (low near voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 08:51
S3	33241	S2 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 08:51
S4	24477	S3 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 08:52
S5	15772	S4 not (@ad>"20020418" or @rlad>"20020418")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 16:15
S6	4	S5 and ("high-k" near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 08:54

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S7	250	toledo.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 08:54
S8	10	("5550079" "5710072" "5897349" "5981320" "6225155" "6258647" "6436749" "6495408" "6506647" "6524904").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/04 10:03
S9	9	("4957877" "5254489" "5480828" "5502009" "6033943" "6080682" "6143669" "6165846" "6300197").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/04 10:07
S10	5	("5358894" "5497021" "5502009" "5869385" "6040019").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/04 10:09
S11	3	("6143669").URPN.	USPAT	OR	OFF	2006/08/04 10:10
S12	1021	(438/770).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 10:33
S13	6855	(gate near dielectric) same ("high-k" or (high))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 14:01
S14	4399	(gate near dielectric) with ("high-k" or (high))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 10:36
S15	1840	(gate near dielectric) with ("high-k" or (high near (k or constant)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 10:37
S16	560	S15 and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 10:38
S17	467	S15 not (@ad>"20020418" or @rlad>"20020418")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 14:01

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S18	164	S17 and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/04 10:38
S19	3	("6013553" "6020024" "6048769").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/04 11:33
S20	1840	(gate near dielectric) with ("high-k" or (high near (k or constant)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 12:00
S21	184	S20 not (@ad>"20020418" or @rlad>"20020418") and (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 12:06
S22	26	S20 not (@ad>"20020418" or @rlad>"20020418") and ((high and low) near voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/05 12:06
S23	3815	((257/369) or (257/371) or (438/275)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 14:01
S24	2947	S23 not (@ad>"20020418" or @rlad>"20020418")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 14:01
S25	114	S24 and (gate near dielectric) same ("high-k" or (high))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/06 16:15
S26	12	("5960289" "6087229" "6093590" "6114203" "6133130" "6140185" "6165849" "6184072" "6184114" "6200865" "6221712" "6291282").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/06 14:08
S27	10	("5254489" "5327002" "5464783" "5497021" "5502009" "5576226" "5716863" "5716864" "5763922" "5821172").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/06 14:31

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S28	84	("5960289").URPN.	USPAT	OR	OFF	2006/08/06 14:31
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